

Features

- Frequency: 27GHz~30GHz
- Gain: 26dB
- Output P_{1dB}: 35.5dBm
- Supply Voltage: +6V
- Power-Added Efficiency: 20%
- Package Size: 6mm×6mm×1.2mm

Typical Applications

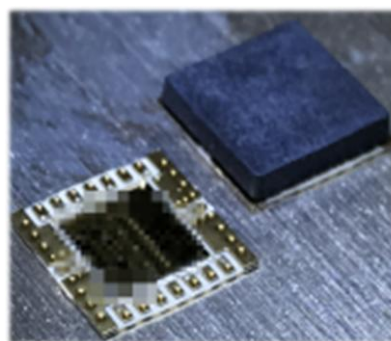
- Microwave radio
- Telecommunication
- Test instrumentation
- SATCOM
- VSAT

General Description

The XT3118Q6 is a KA band GaAs MMIC power amplifier. The XT3118Q6 provides 26dB of gain, and 35.5dBm of output power for 1 dB compression and 20% PAE from a +6V supply.

The XT3118Q6 is a GaAs MMIC power amplifier housed in a 6x6 mm surface mount package. XT3118Q6 is ideal for SATCOM, test equipment applications, Point to Point radio and radar applications.

Image



Electrical Performance

T_A=25°C, V_D=+6V, I_{DQ}=2A, Z₀=50Ω, CW Fixture Test

Parameter	Min.	Typ.	Max.	Units
Frequency Range	27~30			GHz
Small Signal Gain	23	26	—	dB
Small Signal Gain Flatness	—	±2	—	dB
Reverse Isolation	—	-40	—	dB
Input Return Loss	—	-10	—	dB
Power-Added Efficiency	—	20	—	%
Output Power for 1 dB Compression (OP _{1dB})	35	35.5	—	dBm
Output Third Order Intercept(OIP ₃)*	—	39	—	dBm
IM ₃ ***	—	-24	—	dBc
Drain Voltage(V _D)	—	6	6.3	V
Gate Current(I _G)	—	5	28	mA
Supply Current(I _D)	—	3.5	4.2	A
Thermal Resistance **	—	4.1	—	°C/W

*Pout / Tone = 22dBm, fc= 29GHz, Δf=1MHz

**The device is soldered on Ro4350b t=0.168mm, with 81 filled metal vias for grounding.

*** Pout / Tone = 27dBm, fc= 29GHz, Δf=1MHz

Absolute Maximum Ratings

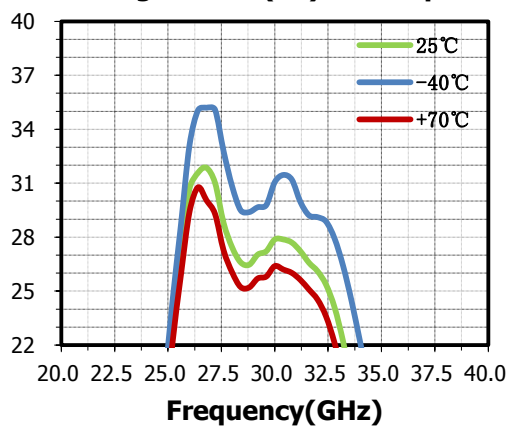
Maximum Input Power	+14dBm	Operating Temperature	-40℃~+70℃
Channel Temperature	165℃	Storage Temperature	-65℃~+150℃
Maximum V_D	+6.5V	Maximum V_G	-1.2V

Typical Performance Curve

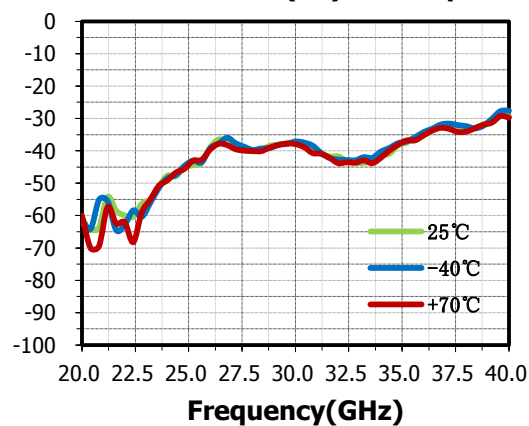
The results captured in the test-jig environment within connector plane

$V_D=+6v$ $I_D=2A$ CW

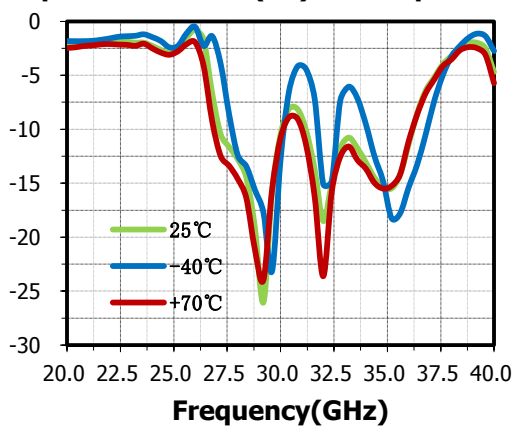
Small Signal Gain(dB) vs.Temperature



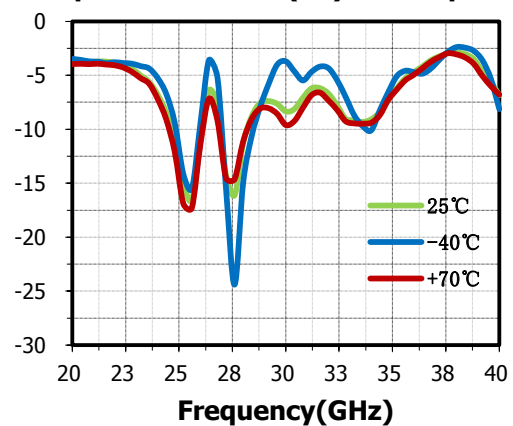
Reverse Isolation(dB) vs.Temperature



Input Return Loss(dB) vs.Temperature



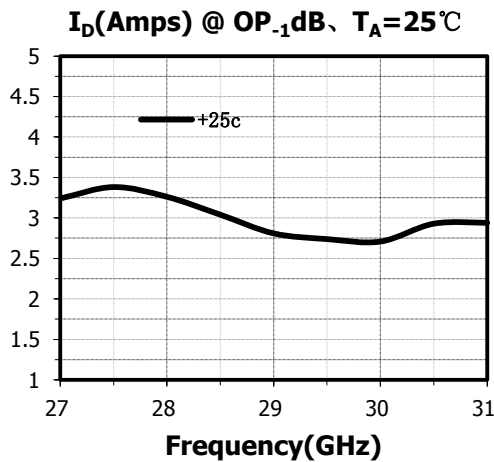
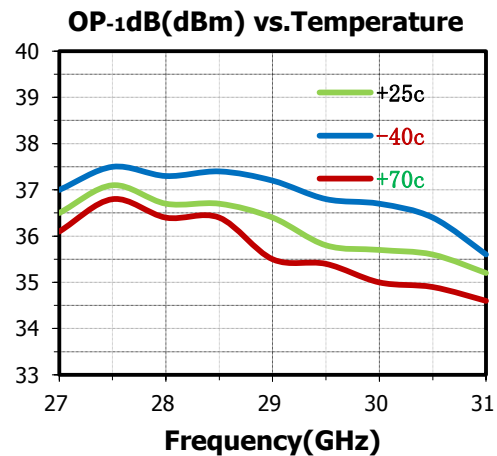
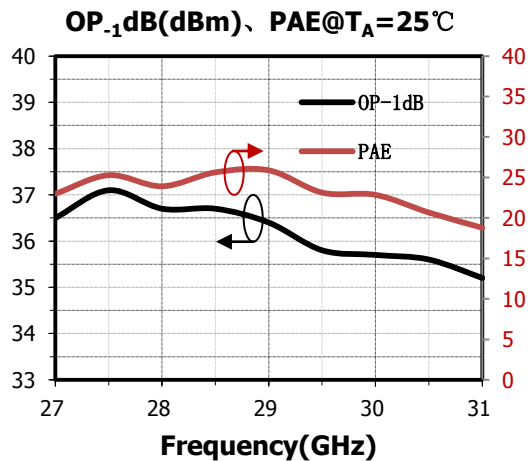
Output Return Loss(dB) vs.Temperature



Power and PAE Performance Curve

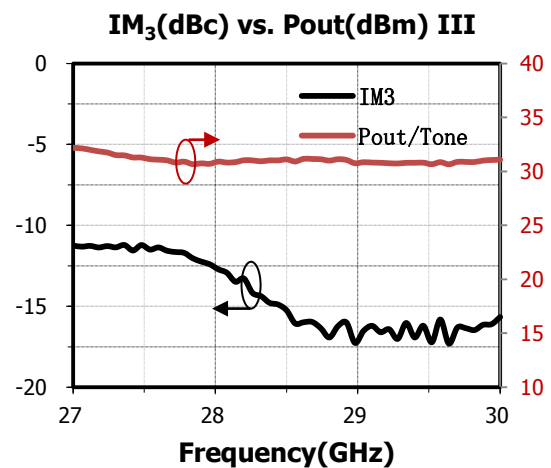
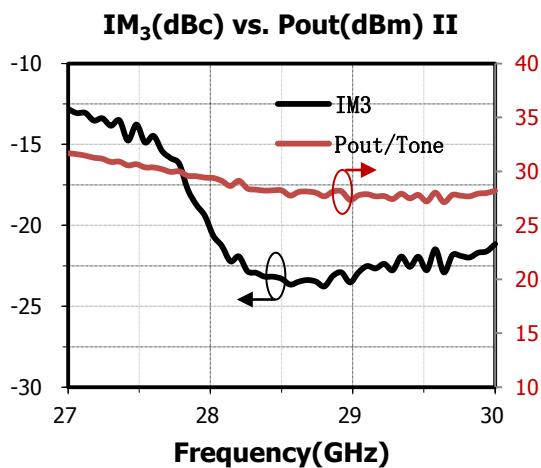
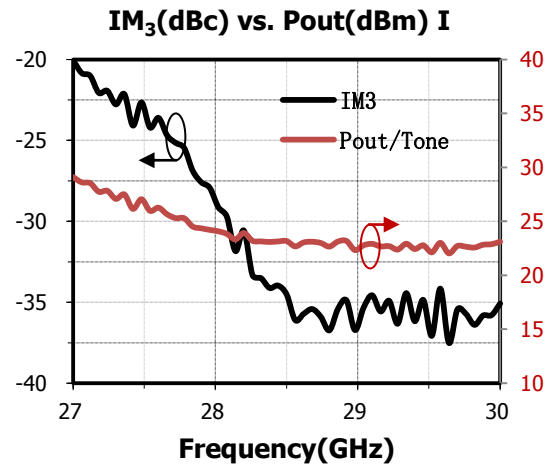
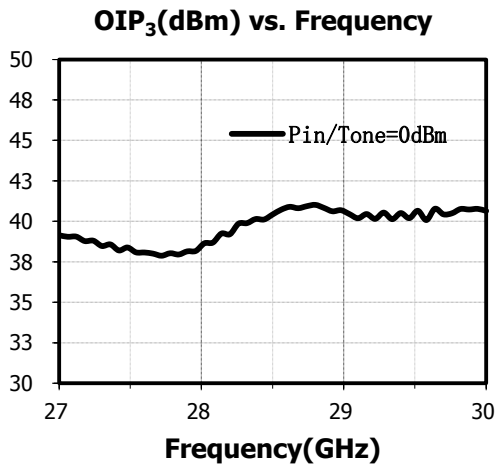
The results captured in the test-jig environment within connector plane, then de-embedded the housing and come back in the die plane

$V_D = +6V$ $I_D = 2A$ CW



OIP₃ 、IM₃ Performance Curve

The results captured in the test-jig environment within connector plane, then de-embedded the housing and come back in the die plane



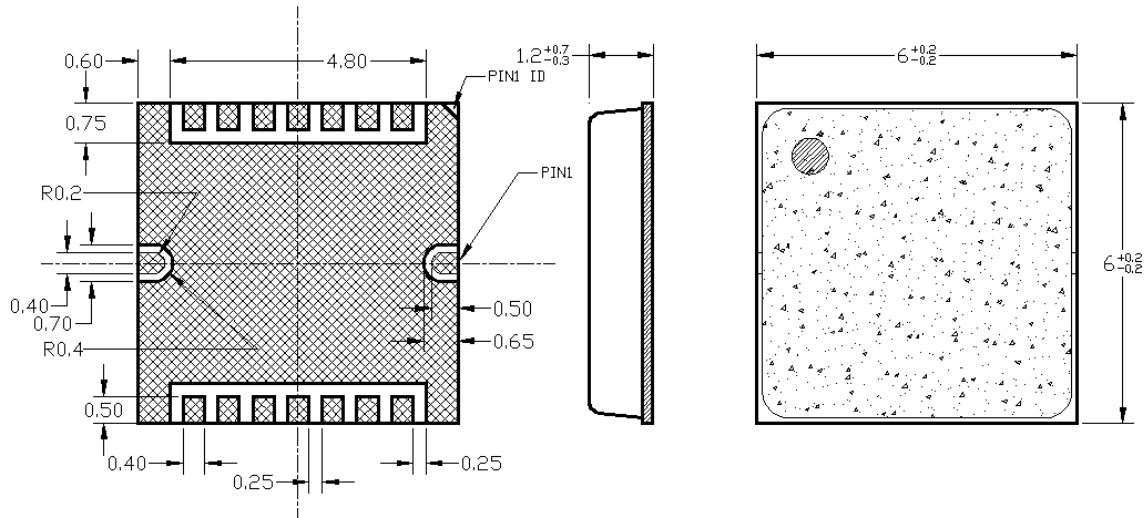
XT3118Q6



GaAs MMIC Power Amplifier
27GHz~30GHz 35.5dBm

Rev 2.2

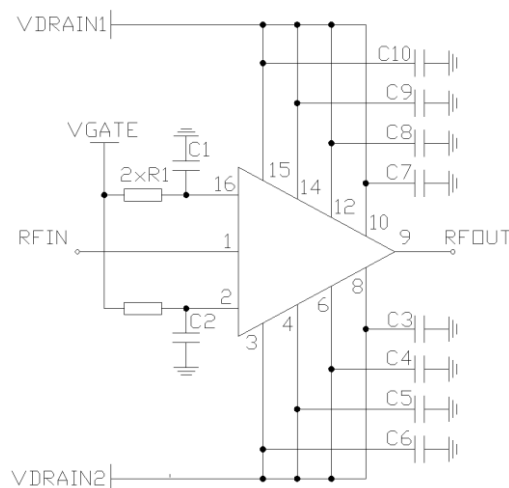
Outline Drawing(mm)



Pin Descriptions

Pin No.	function	Pin No.	function
1	RF Input, Internal grounding	9	RF Output, AC coupled
2	Gate1 A	10	Drain 4B
3	Drain A	11	NC
4	Drain 2 A	12	Drain 3B
5	NC	13	NC
6	Drain 3 A	14	Drain 2B
7	NC	15	Drain 1B
8	Drain 4A	16	Gate 1 B

Application Circuit

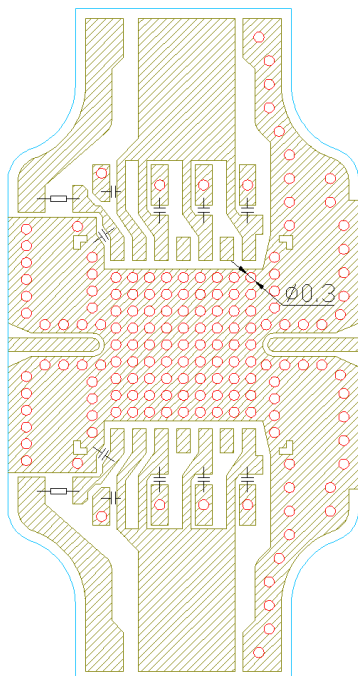


List of Material

Reference Des.	Value	Part Number	Manuf.	Size
C1~C2	2.2uF	GRM033R61A225KE47D	Murata	0201
C3~C10	0.047uF	GRM033R61A473KE47D	Murata	0201
R1*	20Ω	—	ANY	0603

*The value of R1 is related the internal resistance of gate bias circuit, when the internal resistance of the gate bias circuit is less than 2 Ohms, set the R1 to 15--30 Ohms.

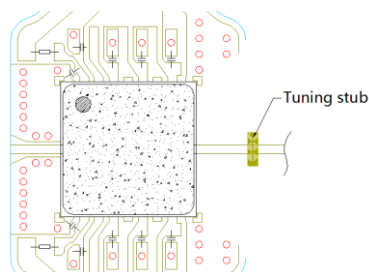
XT3118Q6 test fixture layout



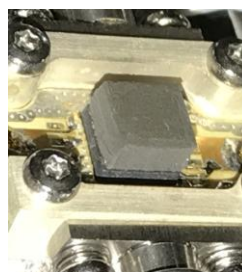
- PCB substrate: RO4350B, Thickness of substrate: 0.254mm
- Electronic copy of board design documents are available for reference.

Recommended use of this chip with special attention

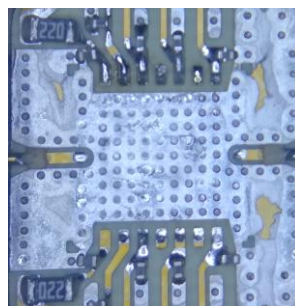
- It is highly recommended to reserve a micro-strip line at the output of device, it will be used for fine tune of output power .etc



- If there is resonance, try to put some absorbing material at the top of the device.



- Put all de-coupling capacitors as closer as possible to the device.
- In order to prevent the device being destroyed by bad heat dissipation, make sure most of the ground via be filled with solder paste once device soldering work has been done.



- Use thin PCB board to short the thermal dissipation path.